

STATE-Senri

Yoshitada MORIKAWA

*The Institute of Scientific and Industrial Research (ISIR)
Osaka University*

morikawa@sanken.osaka-u.ac.jp

First-principles Electronic Structure Theory

- Understand important factors determining properties of materials.
- Predict properties of new materials.
- Design new desired materials.

First-principles Electronic Structure Theory

- Based on basic principles of physics such as quantum mechanics, electromagnetism, and statistical mechanics.
- It does not depend on experimentally fitted parameters.
- Electronic structures of materials can be accurately reproduced by computer simulations.

STATE-Senri

(Simulation Tool for Atom TEchnology)

- Density Functional Theory
LDA, GGA, LDA+U
 - Ultrasoft pseudopotential
 - Plane wave basis set
 - Iterative diagonalization
Davidson method, RMM-DIIS method
 - Broyden charge density mixing
- > Applicable to wide range of materials.

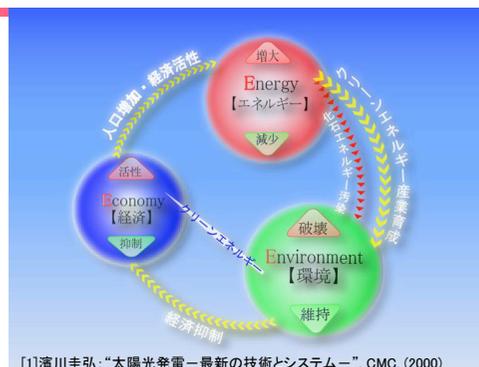
STATE-Senri

(Simulation Tool for Atom TEchnology)

- Structure Optimization
- Finite Temperature Molecular Dynamics
- Reaction Path Search
- Vibrational Spectra (IR, HREELS)、Electronic States (XPS, UPS)、STM Image calculations

3E-trilemma

- **Economy**
- **Energy**
- **Environment**



Solve the trilemma by Quantum Simulations.

STATE-Senri

(Simulation Tool for Atom TEchnology)

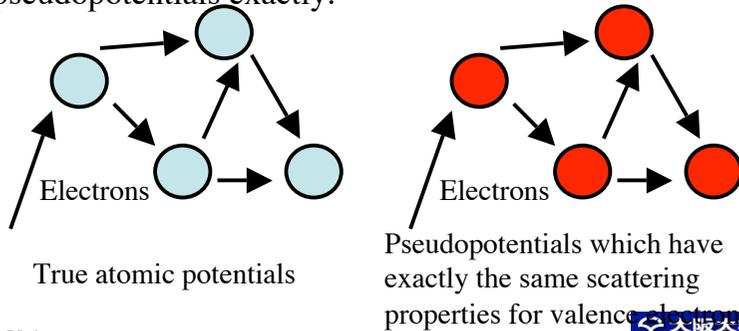
- Tutorial course in “Computational Materials Design (CMD) Workshop”.
<http://www.dyn.ap.eng.osaka-u.ac.jp/CMD14/>
- Twice a year in CMD-WS(Mar. and Sep.).
- Open to both theoretical and experimental researchers.
- Open to Asian researchers and students.

Pseudopotential Method

- **Core Electrons**: Tightly bound to nuclei
--> Localized close to nuclei.
- **Valence Electrons**: Weakly bound to nuclei
--> Delocalized around neighboring atoms.
- **Physical and chemical properties** of materials should be mainly governed by the **valence electron states**.
--> **Necessary to reproduce valence electron states accurately.**

Concept of Pseudopotential

- Atom : Scattering potential of electrons.
- Core electrons are localized within spheres of radius r_c
- If the scattering properties of pseudopotentials outside of radius r_c are the same as those of true atomic potentials, then the valence electron states should be reproduced by pseudopotentials exactly.



Norm-conserving pseudopotentials

To construct norm-conserving pseudopotentials, we first perform all-electron calculation for an isolated atom and obtain energy eigenvalues ϵ_l , wave functions $\psi_l(r)$, and, self-consistent effective potential $V^{AE}(r)$. l is an angular momentum quantum number of a valence state. satisfies the following Kohn-Sham equation.

$$(T + V^{AE}(r))\psi_l(r) = \epsilon_l\psi_l(r),$$

$$T = -\frac{1}{2r^2} \frac{d}{dr} r^2 \frac{d}{dr} + \frac{l(l+1)}{2r^2},$$

$$\langle \psi_l | \psi_l \rangle = \int_0^\infty |\psi_l(r)|^2 r^2 dr = 1.$$

Advantages of the pseudopotential method

- It is as **accurate** as an all-electron full-potential linearized augmented plane wave (FLAPW) method for valence states.
- It is **computationally fast** because it does not calculate core states explicitly.
- Required number of **effective digits** can be smaller compared with all-electron methods because it does not treat core states of which energies have large absolute values.
- Pseudopotentials and pseudowave functions are smooth and can be expanded by **plane wave basis sets** efficiently.

Costruction of pseudo wave function

Next, we construct pseudowave function $\varphi_l(r)$ by smoothing true wave function $\psi_l(r)$ inside the cutoff radius of r_{cl} . Usually, we expand $\varphi_l(r)$ by polynomial functions inside the r_{cl} .

$$\varphi_l(r) = \begin{cases} \psi_l(r) & \text{for } r \geq r_{cl} \\ \sum_{t=0}^M c_{l,2t} r^{2t+l} & \text{for } r \leq r_{cl} \end{cases}$$

Two more constraints are imposed on $\varphi_l(r)$

- They are nodeless inside r_{cl}
- The norm-conserving condition:

$$\int_0^{r_{cl}} |\psi_l(r)|^2 r^2 dr = \int_0^{r_{cl}} |\varphi_l(r)|^2 r^2 dr.$$

The norm-conserving condition is very important to ensure the accuracy of pseudopotentials.

Construction of pseudopotentials

By solving the Kohn-Sham equation inversely, pseudo-potential $V_l(r)$ which acts pseudo-wave function $\varphi_l(r)$.

$$V_l(r) = \frac{(\varepsilon_l - T)\varphi_l(r)}{\varphi_l(r)}$$

Pseudopotentials become angular momentum dependent and therefore, they are non-local. Usually, angular momentum dependence are taken into account only up to $l=2$ and pseudopotentials for $l>2$ are replaced by a common potential $V_{loc}(r)$.

$$V^{ps} = \sum_{l,m=0}^{l=\max, m=l} |Y_{lm}\rangle (V_l(r) - V_{loc}(r)) \langle Y_{lm}| + V_{loc}(r)$$

where, $|Y_{lm}\rangle$ are projectors onto states with angular quantum numbers of l and m momentum.

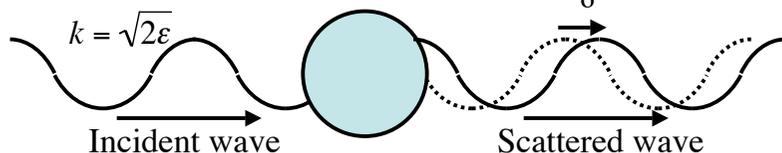
The norm-conserving condition

The norm-conserving condition can be related to logarithmic derivatives of wave functions by the following equation.

$$\int_0^{r_c} |\psi_l(r)|^2 r^2 dr = \int_0^{r_c} |\phi_l(r)|^2 r^2 dr = -\frac{1}{2} (r\phi_l(r))^2 \frac{d}{d\varepsilon} \frac{d}{dr} \ln \phi_l(r) \Big|_{r_c}$$

The logarithmic derivatives of wave functions can be related to phase shifts of scattered wave functions by spherical potentials.

$$\frac{d}{dr} \ln \phi_l(r) \Big|_{r_c} = \frac{k [j_l'(kr_c) \cos \delta_l - n_l'(kr_c) \sin \delta_l]}{j_l(kr_c) \cos \delta_l - n_l(kr_c) \sin \delta_l}$$



Norm-conserving Pseudopotential

The norm-conserving pseudopotentials are constructed by imposing the following three conditions.

1. They reproduce correct eigenenergies ε_l for valence electrons.
2. Pseudo-wave functions coincide with all-electron wave functions outside the cutoff radii r_{cl} .
3. Pseudo-wave functions have correct norm inside the cutoff radii r_{cl} .

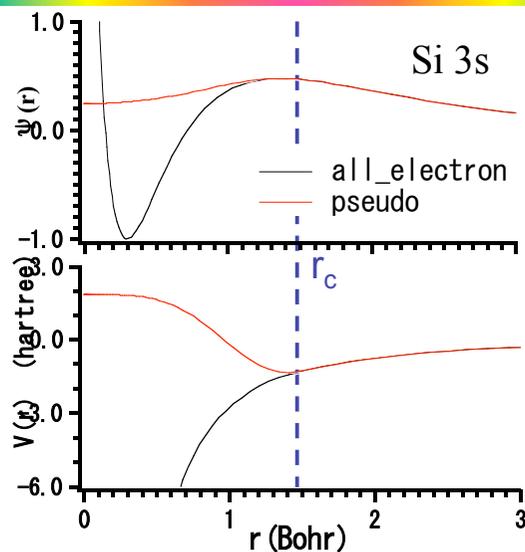
$$4\pi \int_0^{r_c} |\psi_l^{AE}(r)|^2 r^2 dr = 4\pi \int_0^{r_c} |\psi_l^{ps}(r)|^2 r^2 dr$$

$$= -2\pi (r\psi_l^{AE})^2 \frac{d}{d\varepsilon} \frac{d}{dr} \ln \psi_l^{AE} \Big|_{r_c}$$

The norm-conserving condition

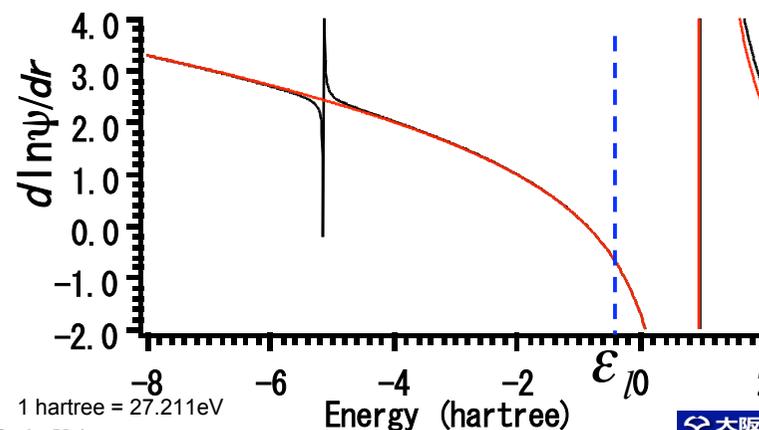
A pseudo-wave function $\varphi_l(r)$ is constructed in such a way that it has the correct scattering property at the eigen energy ε_l outside the cutoff radius r_{cl} . By imposing the norm-conserving condition, the scattering property becomes correct not only at the eigen energy ε_l but also at other energies ε up to the first order of $\varepsilon - \varepsilon_l$. Therefore, the norm-conserving condition is very important to ensure the accuracy of pseudopotentials.

Norm-conserving pseudopotential



Norm-conserving pseudopotential

- The logarithmic derivative of pseudo-wave function agrees with that of true wave function in wide range of energy.



Plane Wave Basis Set

- Pseudopotentials and pseudo-wave functions can be expanded by plane waves efficiently because they are quite smooth.

$$|\psi_{i,\mathbf{k}}\rangle = \sum_{\mathbf{G}}^{|\mathbf{k}+\mathbf{G}| \leq G_{\max}} c_{i,\mathbf{k}+\mathbf{G}} |\mathbf{k} + \mathbf{G}\rangle,$$

$$\langle \mathbf{r} | \mathbf{k} + \mathbf{G} \rangle = \frac{1}{\sqrt{\Omega_a}} \exp(i(\mathbf{k} + \mathbf{G}) \cdot \mathbf{r}),$$

Ω_a : Unit cell volume

$$\langle \mathbf{k} + \mathbf{G} | \mathbf{k}' + \mathbf{G}' \rangle = \delta_{\mathbf{k}\mathbf{k}'} \delta_{\mathbf{G}\mathbf{G}'}$$

Cutoff Wavenumber (Cutoff Energy)

The number of reciprocal points \mathbf{G} used in plane wave expansion is, in principle, infinite. However, in practice, it should be finite and the summation with respect to \mathbf{G} should be cutoff. Usually, we cutoff \mathbf{G} in such a way that **the norm of $\mathbf{k}+\mathbf{G}$ is smaller than a cutoff wave number G_{\max} .**

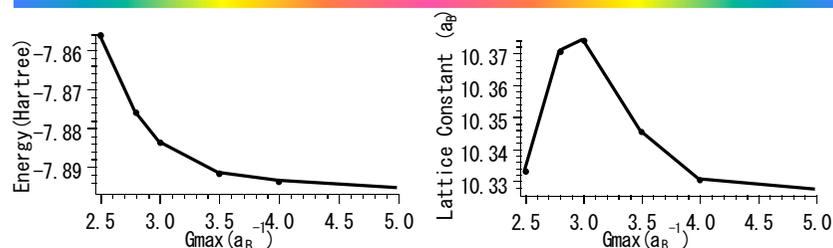
$$\psi_{i\mathbf{k}}(\mathbf{r}) = \sum_{\mathbf{G}}^{|\mathbf{k}+\mathbf{G}| \leq G_{\max}} c_{i\mathbf{k}+\mathbf{G}} \frac{1}{\sqrt{\Omega}} \exp(i(\mathbf{k} + \mathbf{G}) \cdot \mathbf{r}),$$

$c_{i\mathbf{k}}$ is a Fourier transform of $\psi_{i\mathbf{k}}(\mathbf{r})$.

$$c_{i\mathbf{k}+\mathbf{G}} = \frac{1}{\sqrt{\Omega}} \int_{\Omega} \exp(-i(\mathbf{k} + \mathbf{G}) \cdot \mathbf{r}) \psi_{i\mathbf{k}}(\mathbf{r}) d\mathbf{r}.$$

$2\pi/G_{\max}$ corresponds to **the spacial resolution** of the basis set. Therefore, the required G_{\max} depends on **the steepness of pseudo-wave functions**. **G_{\max}^2 is called "Cutoff Energy".**

Cutoff Wavenumber: Example Si



By using $G_{\max}=3.5 a_B^{-1}$, the total energy is converged within 0.1 eV and the lattice constant is within 0.001 nm. In general, energy differences among different structures converge better than the absolute values of total energies.

1 Hartree = 27.2116 eV

Problem in Norm Conserving Pseudopotentials

- Nodeless wave functions such as O2p and Cu 3d.
- Wave functions have large amplitude close to nuclei.
- To satisfy the norm-conserving condition, pseudo-wave functions should also have large amplitude near nuclei.
- The required number of plane waves to expand steep pseudo-wave functions becomes large and calculations become very heavy.

Advantages of Plane Wave Basis Set

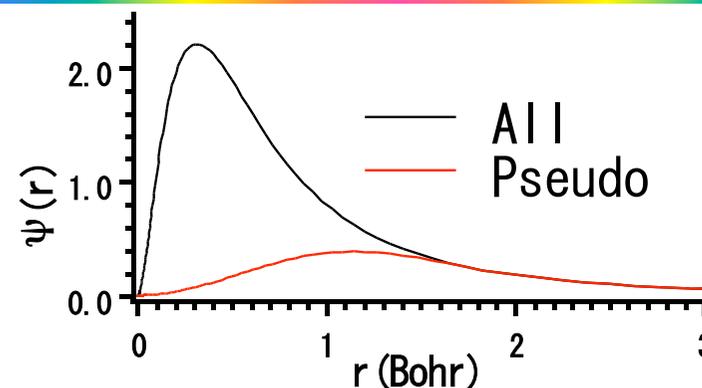
- The size of a plane wave basis set can be enlarged systematically by increasing the cutoff G_{\max} .
--> No Over Completeness Problem!
- The whole space can be covered with the same accuracy.
--> No Basis Set Superposition Error!
- Atomic forces can be easily calculated because of the Hellmann-Feynman theorem for the derivative of the total energy with respect to atomic positions.

$$\mathbf{F}_I = -\frac{d}{d\mathbf{R}_I} E_T$$

$$= -\sum_{ik} f_{ik} \langle \psi_{ik} | \frac{\partial}{\partial \mathbf{R}_I} (V_{\text{loc}}^{\text{ion}} + V_{\text{NL}}) | \psi_{ik} \rangle - \frac{d}{d\mathbf{R}_I} E_{\text{EW}}$$

- Very efficient FFT can be used.

Ultrasoft Pseudopotential



- By removing the norm-conserving condition, pseudo-wave functions can be very smooth.

→ Ultrasoft Pseudopotential

Generalized Norm-conserving Condition

$$4\pi \int_0^{r_c} |\psi_l^{AE}(r)|^2 r^2 dr = \langle \psi_l^{AE} | \psi_l^{AE} \rangle_{r_c} = \langle \psi_l^{PS} | S | \psi_l^{PS} \rangle_{r_c}$$

$$= -2\pi (r\psi_l^{PS})^2 \frac{d}{d\varepsilon} \frac{d}{dr} \ln \psi_l^{PS} \Big|_{r_c},$$

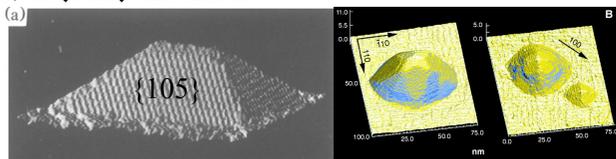
Generalized Norm-conserving Condition

$$S = 1 + \sum_{nm} q_{nm} |\beta_n\rangle \langle \beta_m|, \quad \langle \psi_l^{PS} | \beta_m \rangle = \delta_{lm}.$$

$$H|\psi_l^{PS}\rangle = \varepsilon_l S|\psi_l^{PS}\rangle. \quad \text{Generalized Eigen Value Problem}$$

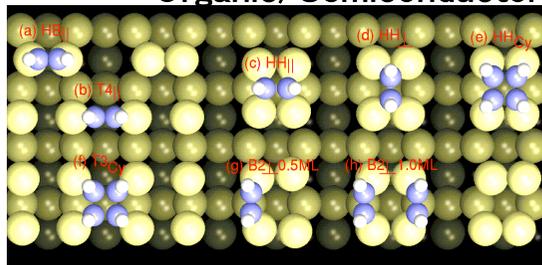
Examples: Semiconductor Surfaces

Ge/Si(105) surface

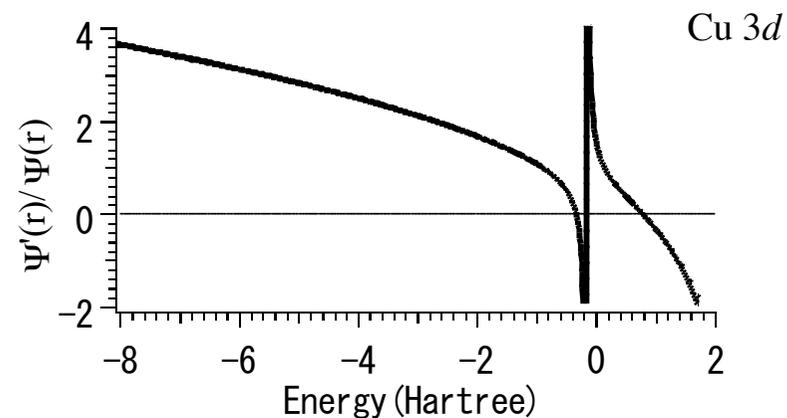


Ge/Si(105): Surface

Organic/Semiconductor

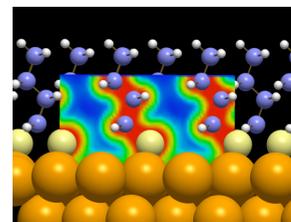


Ultrasoft Pseudopotential

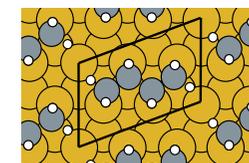


The accuracy of pseudopotentials can be improved further by employing multiple reference states.

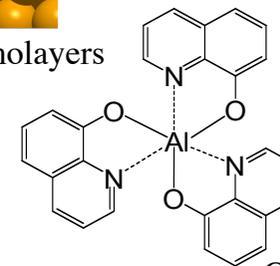
Examples of calculations



Self-assembled monolayers

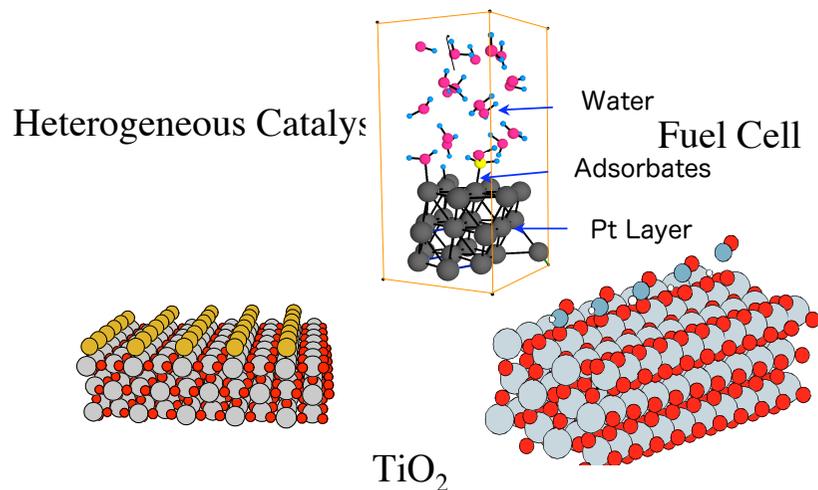


n-alkane/metal



Organic EL

Examples of calculations



全エネルギー

$$E_{XC} = \int \varepsilon_{xc}(\mathbf{r}) \rho(\mathbf{r}) d\mathbf{r},$$

$$E_{loc} = \int V_{loc}^{ion}(\mathbf{r}) \rho(\mathbf{r}) d\mathbf{r} = \Omega_a \sum_{\mathbf{G}}^{|G| \leq 2G_{max}} V_{loc}^{ion}(\mathbf{G}) \rho^*(\mathbf{G}),$$

$$E_{NL} = \sum_{ik} f_{ik} \sum_{Inm} D_{nm}^{ion} \langle \psi_{ik} | \beta_n \rangle \langle \beta_m | \psi_{ik} \rangle,$$

$$E_{EW} = \frac{1}{2} \sum_{I \neq J} \frac{Z_I Z_J}{|\mathbf{R}_I - \mathbf{R}_J|}.$$

全エネルギー

$$E_T = E_K + E_H + E_{XC} + E_{loc} + E_{NL} + E_{EW},$$

$$E_K = \sum_{ik} f_{ik} \langle \psi_{ik} | -\frac{1}{2} \nabla^2 | \psi_{ik} \rangle = \sum_{ik} f_{ik} \sum_{\mathbf{G}}^{|k+\mathbf{G}| \leq G_{max}} |c_{ik}|^2 \frac{|\mathbf{k} + \mathbf{G}|^2}{2},$$

$$E_H = \frac{1}{2} \int \frac{\rho(\mathbf{r}) \rho(\mathbf{r}')}{|\mathbf{r} - \mathbf{r}'|} d\mathbf{r} d\mathbf{r}' = \frac{4\pi}{2} \Omega_a \sum_{\mathbf{G}}^{|G| \leq 2G_{max}} \frac{|\rho(\mathbf{G})|^2}{|\mathbf{G}|^2},$$

$$\rho(\mathbf{r}) = \sum_{ik} f_{ik} |\psi_{ik}(\mathbf{r})|^2, \quad \rho(\mathbf{G}) = \frac{1}{\Omega_a} \int \rho(\mathbf{r}) \exp(-i\mathbf{G} \cdot \mathbf{r}) d\mathbf{r}.$$

ヘルマン-ファインマン力

- 平面波基底を用いることにより、全エネルギーの原子座標に関する微分に対してヘルマン-ファインマンの定理が成り立ち、原子に働く力の計算が容易となる。

$$\begin{aligned} \mathbf{F}_I &= -\frac{d}{d\mathbf{R}_I} E_T \\ &= -\sum_{ik} f_{ik} \langle \psi_{ik} | \frac{\partial}{\partial \mathbf{R}_I} (V_{loc}^{ion} + V_{NL}) \psi_{ik} \rangle - \frac{d}{d\mathbf{R}_I} E_{EW} \end{aligned}$$

擬ポテンシャル法の利点

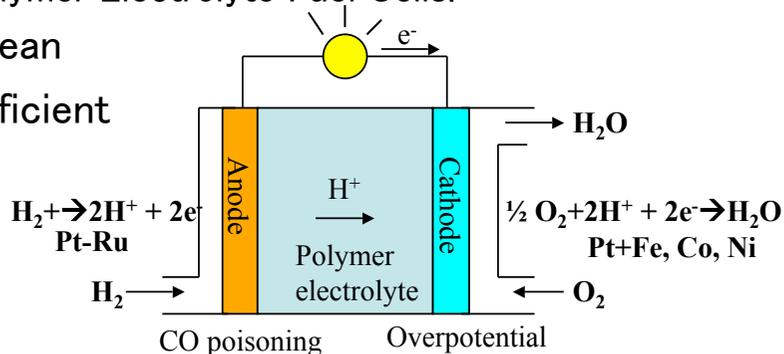
- ・ 価電子の状態に関する限り、精度はフルポテンシャルの全電子計算にほぼ匹敵する。
- ・ 内殻電子を取り扱わず、計算が比較的軽い。
- ・ 絶対値の大きいエネルギーを持つ深い内殻電子を取り扱わないので、全エネルギーの有効桁数が少なくても良い。
- ・ 擬ポテンシャルおよび擬波動関数は滑らかで、平面波基底で容易に展開可。
- ・ 平面波基底によりヘルマン-ファイマンの定理が成り立ち、力の計算が容易。

Fuel Cell

Polymer Electrolyte Fuel Cells.

Clean

Efficient



Electrode metals

•Pt: South Africa74%、Russia14%

→New efficient catalysts are required.

→Necessary to elucidate the reaction mechanisms.

First-principles molecular dynamics simulations of chemical reactions at water/metal interfaces

Y. Morikawa, I. Hamada (*ISIR, Osaka Univ.*)

M. Otani, O. Sugino (*ISSP, Univ. Tokyo*)

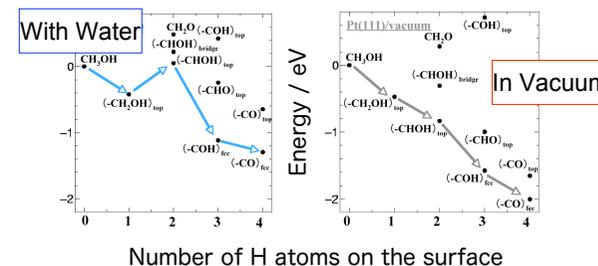
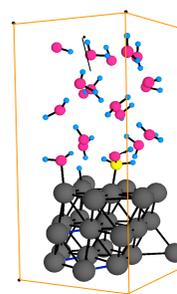
Y. Okamoto (*NEC*)

T. Ikeshoji (*RICS-AIST*)

Chemical Reactions at Water/Metal Interface



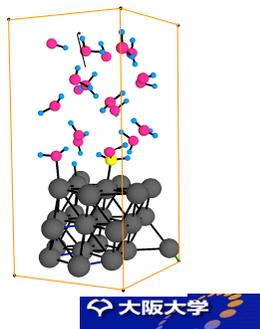
Methanol Oxidation
Stability of Reaction
Necessary to include solvent effects



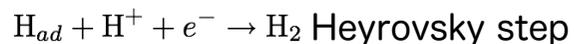
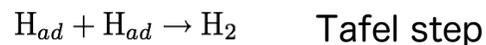
Y. Okamoto, O. Sugino, Y. Mochizuki, T. Ikeshoji, Y. Morikawa,
"Comparative study of dehydrogenation of methanol at Pt(1 1 1)/water
and Pt(1 1 1)/vacuum interfaces"
Chem. Phys. Lett., 377, 238-242 (2003)

Chemical Interactions at Metal/Water Interfaces

- Solvent effects.
- Statistically sample many meta-stable structures.
- Effect of electric field at the interface



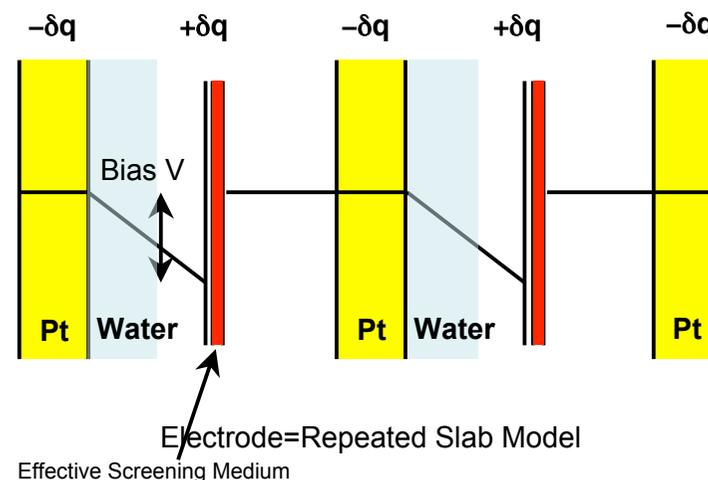
Hydrogen evolution reaction (HER)



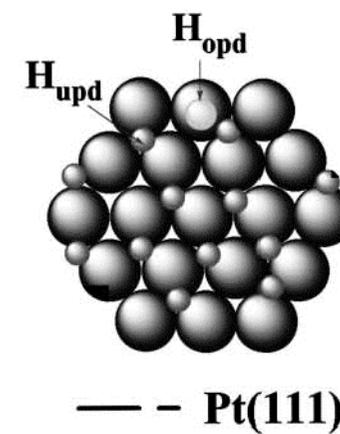
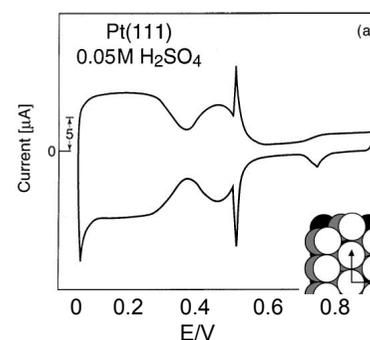
Clarify the Reaction Mechanism

Effective Screening Medium

M. Otani and O. Sugino, Phys. Rev. B 73 115407 (2006)

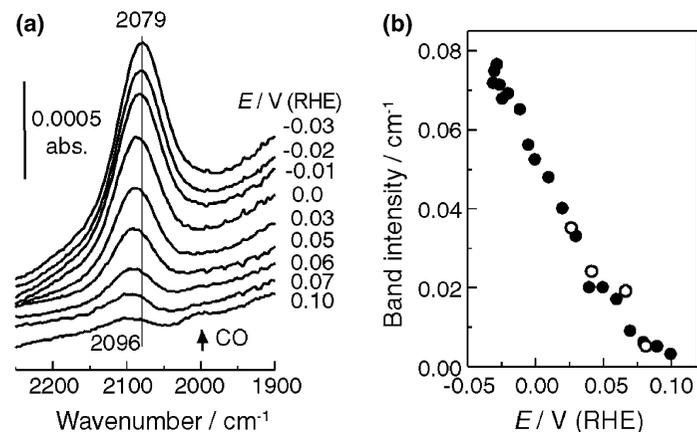


Hupd and Hopd



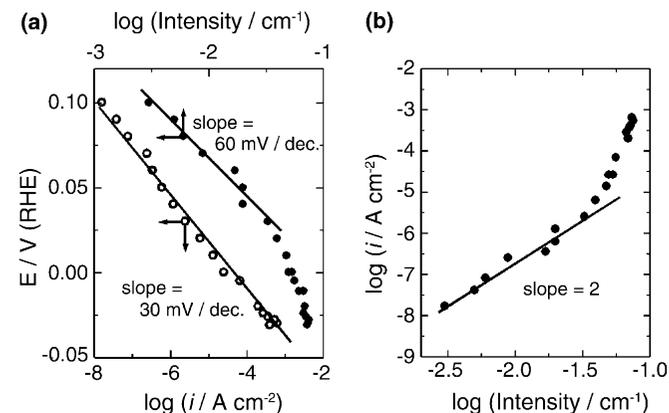
N.M. Markovic and P.N. Ross Jr., Surf. Sci. Rep., 45 117 (2002).

Hydrogen Evolution Reaction on Pt



K. Kunimatsu, T. Senzaki, M. Tsushima, and M. Osawa, Chem. Phys. Lett., 401, 451 (2005).

Hydrogen Evolution Reaction on Pt



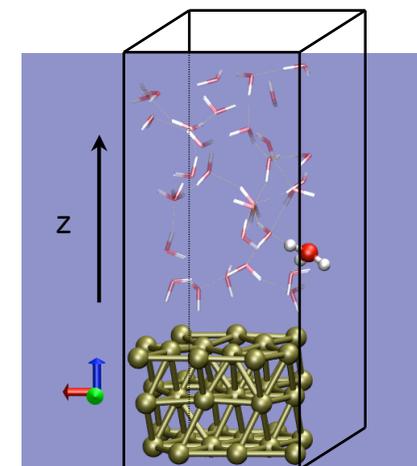
K. Kunimatsu, T. Senzaki, M. Tsushima, and M. Osawa, Chem. Phys. Lett., 401, 451 (2005).

Technicalities

- [STATE \(Simulation Tool for Atom Technology\)](#)
- [Plane wave basis set + ultrasoft pseudopotentials](#)
- [PBE-GGA for exchange-correlation](#)
 - [Cut-off energy](#)
 - [25Ry \(wave functions\)](#)
 - [225Ry \(the augmentation charge\)](#)
- [Born-Oppenheimer MD](#)
 - [Heavy water \(D2O\)](#)
 - [Time step: 1.2 fs](#)
- [ESM \(Effective Screening Medium\) method \(Otani and Sugino, PRB73, 115407 \(2006\)\) to apply the bias voltage](#)

Water/Pt interface model

- 32 H_2O + H^+ (proton)
- Pt(111) ($3 \times 2\sqrt{3}$) surface unit cell
- 3-layer slab (32 atoms)
- Temperature: 353K
- Negatively charged
- +0.25 ~ 0.95 elec.

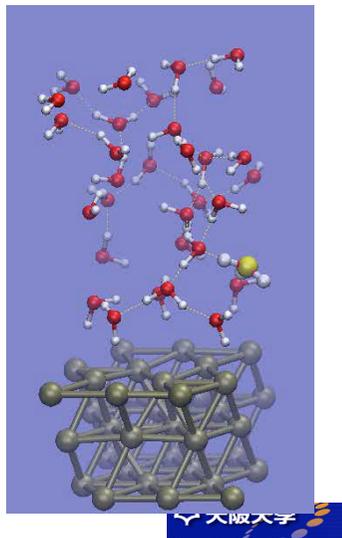


3D-Periodic Boundary Condition

First-principles Molecular Dynamics Simulation of Electrode/Water Interface

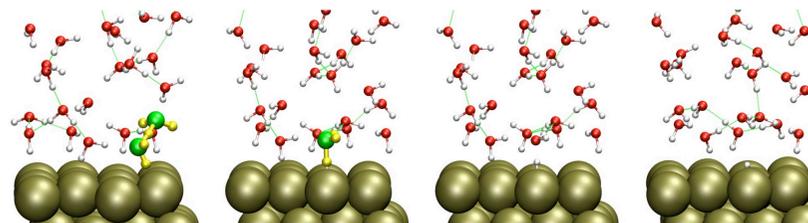
- Total MD simulation time: 3.2 ps
- Added electrons: 0.25-0.40
- 353 K

Red: Oxygen
White: Hydrogen
Yellow: Oxygen in a hydronium ion
Substrate: Platinum



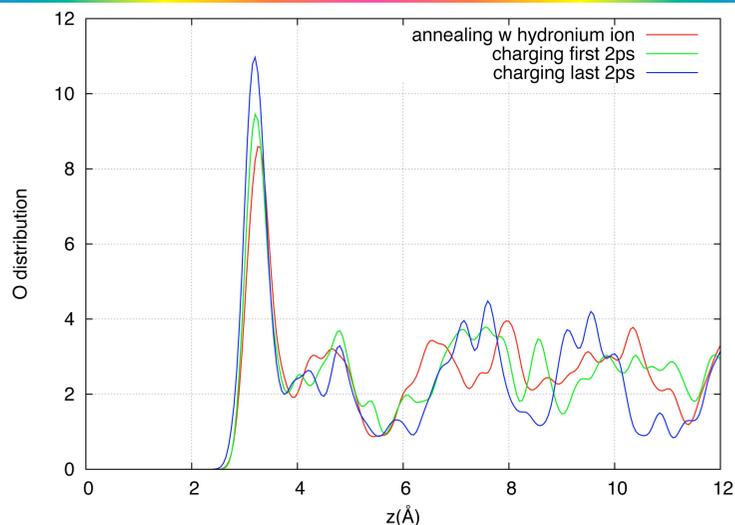
Snapshots

Protons form H_9O_4^+ (Eigen cations), and, H_5O_2^+ (Zundel cations) and diffuse around the interface through the Grotthuss mechanism.



Pt-H connectivity: 2 Å
(NB: Pt-H(atop) distance: ~1.5Å)

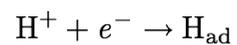
Pt-H radial distribution function



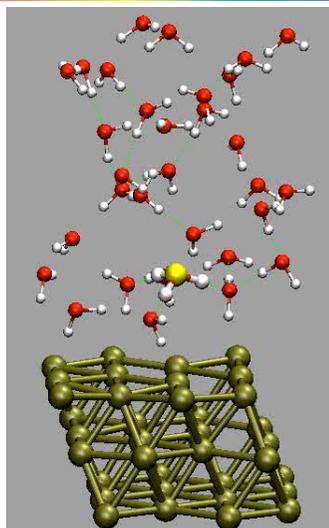
Water Density Near Electrode Surfaces

- Toney et al., *Nature*, **368**, 444 (1994).
water/Ag(111)
1.4 g/cm³ (-0.2 V vs pzc)
2.3 g/cm³ (+0.5 V vs pzc)
- Ito & Yamazaki, *Phys. Chem. Chem. Phys.*, **8**, 3623 (2006).
water/Cu(111)
1.7 g/cm³ (-0.35V vs NHE)
- Present Simulation: water/Pt(111)
1.3 g/cm³ : Low Field ($N_{\text{ex}} = 0.25$)
1.7 g/cm³ : High Field ($N_{\text{ex}} = 1.05$)

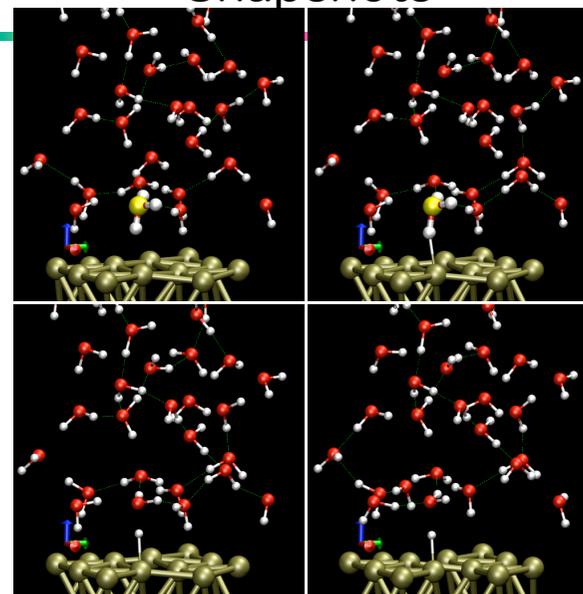
MD simulation of Volmer process



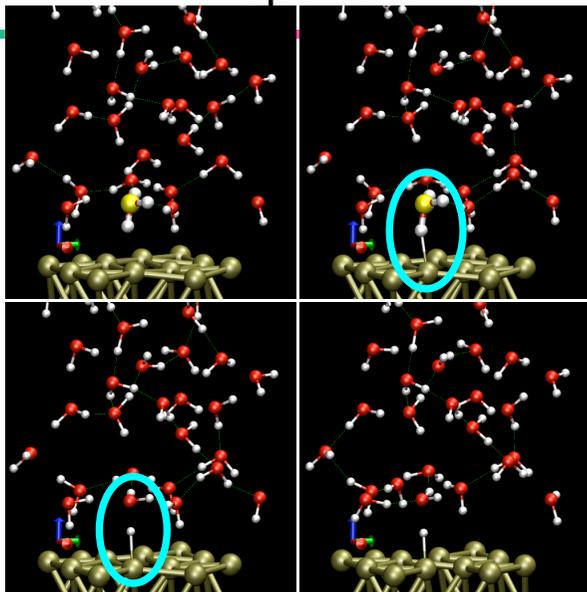
- Total MD simulation time: 2.6 ps
- Added electrons: 0.45-0.95
- 353 K (velocity scaling)



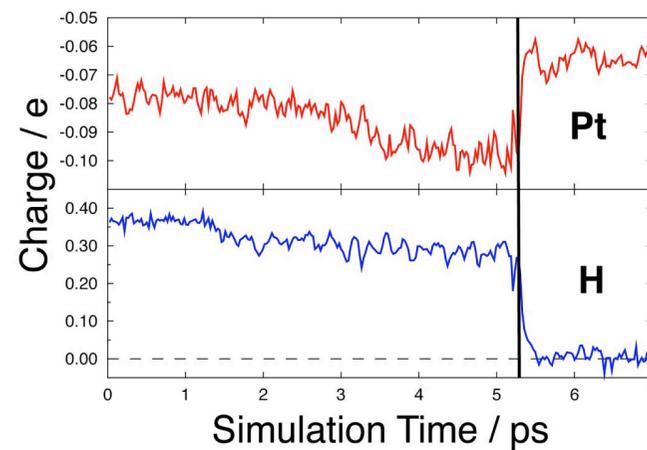
Snapshots



Snapshots

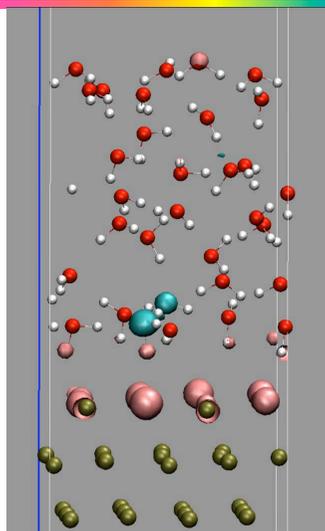


Charge State of Pt and H



Charge Transfer

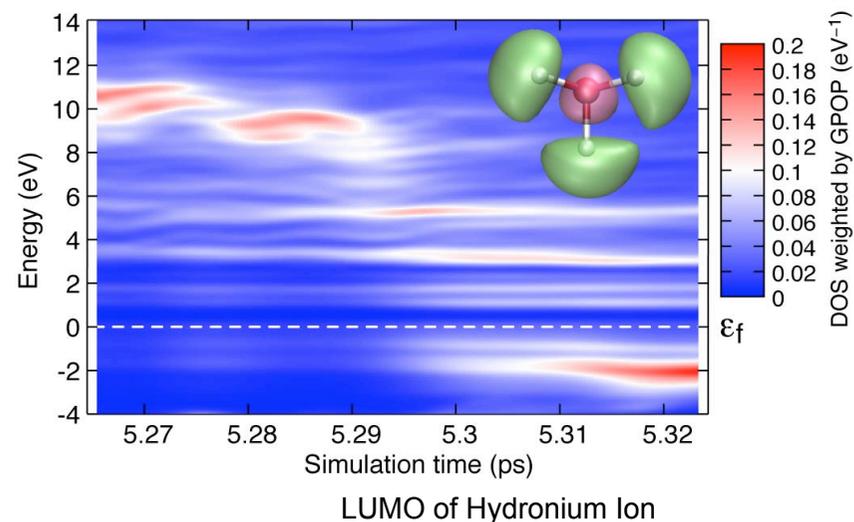
Red: Negatively Charged.
Blue: Positively Charged.



Summary

- Chemical reactions at water/metal interfaces can be successfully simulated by the first-principles molecular dynamics.
- Electric field at the water/metal interface increases the water density significantly.
- Charge transfer process is clarified.

Mulliken Population Analysis



Input file: nfnp_1

- **ENERGY_CUTOFF_FOR_WAVEFUNCTION**

The cutoff energy of plane wave basis set for wave functions.

- **ENERGY_CUTOFF_FOR_CHARGE**

The cutoff energy of plane wave basis set for charge density.
These cutoff energies depend on pseudopotentials.

Example:

```
pot.Cl_pbe1, pot.Br_pbe1, pot.Ge_pbe1, pot.Si_pbe1
  wave function: 10~16Ry, charge: 100Ry
pot.H_lda3, pot.C_pbe3, pot.O_pbe3,
  wave function: 25Ry, charge: 225Ry
pot.H_lda1, pot.C_pbe1, pot.O_pbe1,
  wave function: 30.25Ry, charge: 400Ry
```

It is necessary to check the dependence of total energies on cutoff.

Input file: nfnfp_1

• INITIAL_CONDITION

How to prepare the initial wave functions.

SCRATCH: Generate from scratch

RESTART: Read from “restart.data” which has the latest date.

• INITIAL_POSITIONS

How to prepare the initial atomic positions.

INPUTS : Read from nfnfp_1.

RESTART : Read from “restart.data” which has the latest data.

GEOMETRY_FILE : Read from “GEOMETRY” which can be modified by text editor.

• TOTAL_STEP

Maximum number of molecular dynamics steps.

• Max_CPU_TIME

Maximum CPU time in seconds.

Input file: nfnfp_1

• ALPHA_MIXTURE

Fraction of new charge density in charge density mixing. 0.3~0.8.

• EXCHANGE_CORRELATION_TYPE

Selection of exchange-correlation function.

GGAPBE : Generalized Gradient Approximation by Perdew, Burke and Ernzerhof, Phys. Rev. Lett. **77** 3865 (1996). (Recommended)

LDAPW91 : Local Density Approximation.

• SPACE_GROUP_NUMBER

Specify the symmetry of the system by the group space number.

• BRAVAIS_LATTICE

Specify the type of Bravais lattice.

SIMPLE, **BODY_CENTER**, **FACE_CENTER**,
A_CENTER, **B_CENTER**, **C_CENTER**,
RHOMBOHEDRAL_CENTER

Input file: nfnfp_1

• WAVEFUNCTION_OPTIMIZE

Choose optimization method.

DAVIDSON : Davidson method.

RMM : Residual-vector Minimization Method.

Davidson scheme is quite stable but computationally less efficient compared with RMM scheme. RMM is very fast but it is less stable compared with Davidson scheme. When you start calculations from scratch wave functions, you should use Davidson scheme for first 5-10 iterations and switch to RMM scheme.

• ENERGY_CRITERIA_CONVERGENCE_ELECTRON

Convergence criteria for wave function optimization.

Recommended values: 0.10D-7~0.10D-8

• NUMBER_OF_CHARGE_MIXING

Number of previous iterations included to estimate updated charge.

Recommended value: 20 for easy systems, 50 for difficult systems.

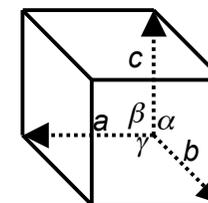
Unit Cell

1) Specify the lengths of the lattice vectors and the angles among them.

&UNIT_CELL

$$\begin{array}{ccc} a & b & c \\ \alpha & \beta & \gamma \end{array}$$

&END_UNIT_CELL



2) Specify the Cartesian coordinates of the lattice vectors.

&UNIT_VECTOR

$$\begin{array}{ccc} ax & ay & az \\ bx & by & bz \\ cx & cy & cz \end{array}$$

&END_UNIT_VECTOR

K-points

```
&NUMBER_K-POINT_MESH_XYZ
```

```
  BROADENING  WIDTH
```

```
  kx  ky  kz
```

```
  1   1   1
```

```
&END_NUMBER_K-POINT_MESH_XYZ
```

Width>0 : Semiconductors or insulators.

Width<0 : Metallic systems.

The absolute value of width should be about 0.002 hartree.

Input file: nfnp_1

```
&COORDINATES
```

```
  Number of atoms  Number of atoms
```

```
  CARTESIAN
```

```
INVERSION_SYMMETRY_COUNTED  NO
```

```
  x  y  z  IWEI  IMDTYP  ITYP
```

```
  x  y  z  IWEI  IMDTYP  ITYP
```

```
  x  y  z  IWEI  IMDTYP  ITYP
```

```
...
```

```
&END_COORDINATES
```

```
IWEI = 1
```

```
IMDTYP = 0 : Fix atomic position
```

```
          1 : Move atomic position
```

```
ITYPE : Atom type number
```

Input file: nfnp_1

```
NUMBER_EIGENVALUES
```

Number of eigen values per spin. Numbers of empty states (10-20) should be included.

```
&ATOMIC_TYPES
```

```
  Number of atomic types
```

```
  Atomic number  mass  spin polarization
```

```
  Atomic number  mass  spin polarization
```

```
...
```

```
&END_ATOMIC_TYPES
```

Structure Optimization and Molecular Dynamics

```
&JOB_TYPE  Job type
```

```
&END_JOB_TYPE
```

QUENCHING: Quenching Molecular Dynamics

This scheme works well when forces acting on atoms are larger than 0.02 hartree/ a_B .

GDIIS: Generalized Direct Inversion of Iterative Subspace

This scheme becomes efficient when the maximum force is smaller than about 0.02 hartree/ a_B .

NORMAL_MODE: Vibration normal mode analysis.

NEB: Nudged Elastic Band Method

Method for reaction path search proposed by Mills, Jonsson, Schenter, *Surf. Sci.* 324 305 (1994).

Structure Optimization and Molecular Dynamics

TIME_STEP

- Increment of time for each step of molecular dynamics simulation. (1 a.u. = 2.4×10^{-17} seconds)
- The time step should be carefully chosen to assure the accuracy of molecular dynamics. It depends on atomic types, maximum forces acting on atoms, and integration scheme of the Newton equation of motion.
- For QUENCHING and NEB schemes, the time step should be 50~300a.u.
- For GDIIS scheme, the time step should be 400~800a.u.
- For NORMAL_MODE, it is not used.
- For FINITE_TEMPERATURE_MD and if the system includes hydrogen, the time step should be about 20a.u. If hydrogen is not included, the time step should be 50~100a.u.

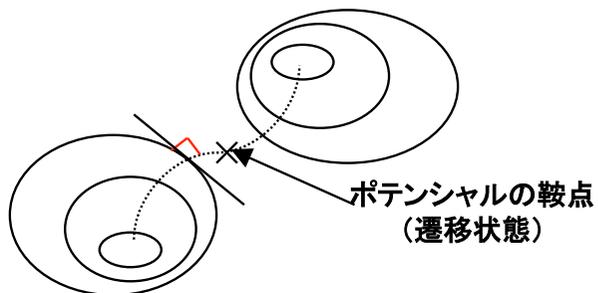
反応経路探索

&JOB_TYPE NEB

&END_JOB_TYPE

NEB: Nudged Elastic Band Method

Mills, Jonsson, Schenter, *Surf. Sci.* **324** 305 (1994).



最小エネルギー経路はポテンシャルの等高線の接線に垂直

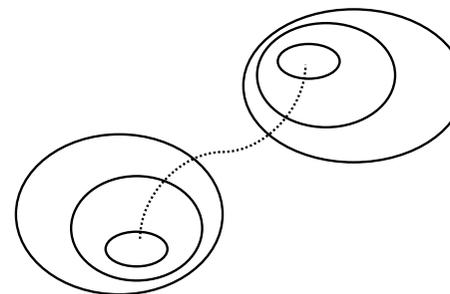
Reaction Path Search

&JOB_TYPE NEB

&END_JOB_TYPE

NEB: Nudged Elastic Band Method

Mills, Jonsson, Schenter, *Surf. Sci.* **324** 305 (1994).



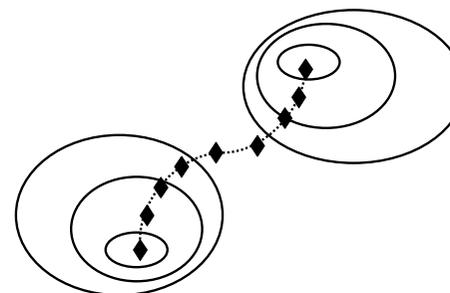
反応経路探索

&JOB_TYPE NEB

&END_JOB_TYPE

NEB: Nudged Elastic Band Method

Mills, Jonsson, Schenter, *Surf. Sci.* **324** 305 (1994).



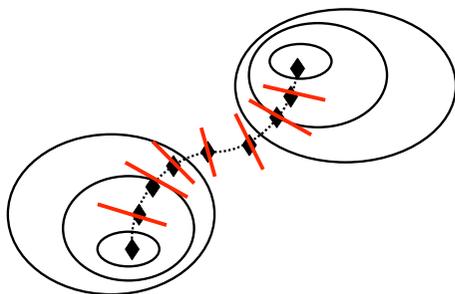
反応経路探索

```
&JOB_TYPE NEB
```

```
&END_JOB_TYPE
```

NEB: Nudged Elastic Band Method

Mills, Jonsson, Schenter, *Surf. Sci.* **324** 305 (1994).



Osaka Univ.



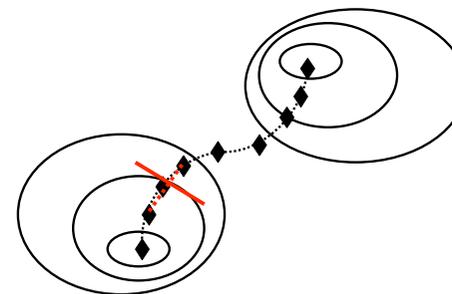
反応経路探索

```
&JOB_TYPE NEB
```

```
&END_JOB_TYPE
```

NEB: Nudged Elastic Band Method

Mills, Jonsson, Schenter, *Surf. Sci.* **324** 305 (1994).

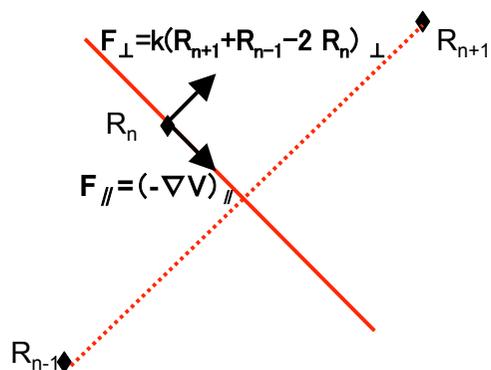


各レプリカを両隣のレプリカを結ぶ直線の垂直二等分面内で最適化

Osaka Univ.



反応経路探索



各レプリカを両隣のレプリカを結ぶ直線の垂直二等分面内で最適化

Osaka Univ.



ジョブの投入

各自のパソコンをRedHatLinuxで起動。

各自のパソコンでログイン名 seminar でログイン。

ターミナルウィンドウを開く。

```
ssh -XI adXX epcs00
```

でPCクラスターシステムにアクセスする。

```
unalias scout
```

```
scout -g pcc -f epcsYY -n 1
```

(YYの部分は各自のプロセッサ番号(01~36)を書く。

```
scrun ./STATE < nfinp_1 >& nfout_1 &
```

Osaka Univ.

